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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 ($T_c=25^\circ\text{C}$)					電 気 的 特 性 ($T_c=25^\circ\text{C}$)										外 形	備 考
				V_{ce0} (V)	V_{be0} (V)	I_c (mA)	P_c (mW)	T_c ($^\circ\text{C}$)	I_{c0} 最大値 (μA)	直流又はパルス h_{FE}		バイアス		h_{FE}	h_{ie} h_{ie}^* (Ω)	h_{re} h_{re}^* ($\times 10^{-4}$)	h_{oe} h_{oe}^* (μS)	$f_{\alpha b}$ $f_{\alpha b}^*$ (Mc)		
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE} , I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB} , I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 $f_{\alpha b}$ OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T .
- 10 C_{ob} AND $r_{bb'}$ OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN $r_{bb'}$ COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

:とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)											外 形	備 考				
				V _{CEO}	V _{EB0}	I _C	P _C	T _J	I _{CHO} 最大値		V _{CE} (V)				I _C (mA)			h _{FE}				f _{ab}	C _{ob}	r _{bb}	
				(V)	(V)	(mA)	(mW)	(°C)	(μA)	V _{CB} (V)	V _{CE} (V)	I _C (mA)	V _{CB} (V)	I _E (mA)	h _{FE}	h _{FE} *	h _{FE} *	h _{FE} *	h _{FE} *						(MHz, 6V, 50μA)
2SA893	日立	RF.AF	Si.E	-90	-5	-50	300	125	-0.5	-75	250-300	-12	-2	-12	2	NF=20dB (1kHz, 6V, 50μA)			120*	1.8	138	2SC1890 とコンパリ			
" 894	新日無	RF	Si.EP	-30	-6	-1A	600	125	-0.5	-20	200	-1	-100	-10	50				150*	25	C _e r _{bb} * 100pS	138			
" 895	"	"	"	-30	-4	-30	200	125	-0.5	-20	100	-6	-1	-10	2				500*	1	C _e r _{bb} * 8pS	138			
" 896	ソニー	"	Si.E	-200	-5	-100	750	120	-0.2	-100	150	-5	-3	-10	10				70*	3	C _e r _{bb} * 50pS	259	2SC1811 とコンパリ		
" 897	"	"	"	-60	-6	-2A	950	120	-0.2	-25	250	-2	-100	-2	10				55*	25	C _e r _{bb} * 350pS	174B			
" 898	富士通	AF.RF	Si.EP	-150	-5	-50	1W	175	-1	-140	150	-5	-50	-5	10				100*	3	70*	328			
" 899	"	"	"	-150	-5	-50	1W	175	-1	-140	150	-5	-50	-5	10				100*	3	70*	328			
" 900	松下	PA	"	-20	-5	-1A	1.2W	150	-1	-10	200	-2	-500	-6	50				200*	40	3.5k*	222	2SC1568 とコンパリ		
" 901	三菱	AF.RF	"	-40	-5	-100	200	125	-0.1	-35	250-1200	-6	-1	-6	1				100*	3.5	C _e r _{bb} * 50pS	138B			
" 902																									
" 903																									
" 904	三菱	AF.RF	Si.EP	-90	-5	-50	200	125	-0.1	-50	250-1200	-6	-1	-6	1				150*	2.5		138B			
" 905	"	"	"	120	-5	-50	800	135	-1	-100	150-800	-10	-10	-10	10				200*	3		242	2SC1915 とコンパリ		
" 906	"	LN	Si.E	-40	-5	-100	200	125	-0.1	-35	250-1200	-6	-1	-6	1	V _{NO} < 200mV (-10V, -1mA, R _C = 100kΩ, G _v = 80dB)			100*	3.5	40	138B			
" 907	サンケン	PA	Si.EMc	-100	-6	-15A	150W (T _J = 25°C)	150	-1mA	-100	80	-4	-5A	-12	500				10*	270	10*	102	2SC1584 とコンパリ		
" 908	"	"	"	-150	-6	-15A	150W (T _J = 25°C)	150	-1mA	-150	80	-4	-5A	-12	500				10*	270	10*	102	2SC1585 とコンパリ		
" 909	"	"	"	-200	-6	-15A	150W (T _J = 25°C)	150	-1mA	-200	80	-4	-5A	-12	500				10	270	10*	102	2SC1586 とコンパリ		
" 910																									
" 911	ソニー	RF	Si.E	-850	-12	-100	470	120	-1.5	-100	50	-5	-10	-10	10	f _a = 650nS, f _{tr} = 500nS f _a = 500nS, f _{tr} = 850nS			9*	8	C _e r _{bb} * 70pS	181	2SC1762 とコンパリ		
" 912	松下	PA	Si.EP	-150	-5	-50	750	135	-1	-100	200	-5	-10	-10	10				200*	3	6k*	165			
" 913	"	RF	"	-150	-5	-1A	15W (T _J = 25°C)	150	-10	-150	150	-10	-150	-10	50				120*	30	3k*	268			
" 914	"	"	"	-150	-5	-50	1W	150	-1	-100	150	-5	-10	-10	10				200*	3	3.5k*	222			
" 915	日電	AF	Si.E	-120	-5	-50	1W	150	-0.1	-120	200	-10	-10	-10	10				80*	2.5		278	2SC1940 とコンパリ		
" 916	"	"	"	-160	-5	-50	1W	150	-0.1	-160	200	-10	-10	-10	10				80*	2.5		278	2SC1941 とコンパリ		
" 917	ソニー	RF	"	-120	-5	-100	750	120	-0.2	-100	150	-5	-3	-10	10				70*	3	C _e r _{bb} * 50pS	259	2SC1951 とコンパリ		
" 918	富士通	"	Si.EP	-40		-300	300	150	-0.1	-10	60	-10	-10	-10	10				200*	4.5	50*	275			
" 919																									
" 920																									
" 921	松下	RF	Si.EP	-120	-5	-20	150	125	-0.1	-50	60	-5	-2	-30	1				200*	3	70	138			
" 922	ソニー	"	Si.E	-80	-6	-1A	625	150	-0.1	-50	150	-2	-100	-10	10				120*	10	C _e r _{bb} * 150pS	84C			